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(54) **PROCESS FOR PRODUCING MULTICRYSTALLINE SILICON INGOTS BY THE INDUCTION METHOD, AND APPARATUS FOR CARRYING OUT THE SAME**

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CPC ***C30B 28/06*** (2013.01); ***C30B 11/003*** (2013.01); ***C30B 11/006*** (2013.01); ***C30B 29/06*** (2013.01); ***C30B 30/04*** (2013.01); ***C30B 35/005*** (2013.01)

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See application file for complete search history.

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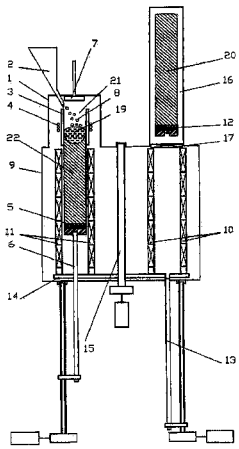
(57) **ABSTRACT**

An apparatus and continuous stable process for producing multicrystalline silicon ingots with large cross-sections by an induction method, by maintaining surface temperature of the ingot at the output of the crucible within the range of 900-1150° C., and by heating the ingot at the output of the upper zone of the controlled cooling compartment to a temperature of 1200-1250° C., followed by cooling of the ingot at a rate of no more than 10° C./cm.

1 Claim, 7 Drawing Sheets